

PATENT

81784.0241

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FORM PTO-1449 INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>										Docket Number (Optional) 81784.0241		Application Number Not Assigned; Parent 09/148,854	
										Applicant: Masayuki KOGA et al.			
										Filing Date August 8, 2001		Group Art Unit Not Assigned	

U.S. PATENT DOCUMENTS												
EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SWL	4	4	6	6	1	7	9	8/84	Kasten			
	5	1	4	5	8	0	8	9/92	Sameshima et al.			
	5	5	2	9	9	5	1	6/96	Noguchi et al.			
	5	5	8	9	4	0	6	12/31/96	Kato et al.	437	21	
	5	5	9	1	6	6	8	1/7/97	Maegawa et al.	437	174	
	5	7	8	9	7	6	3	08/1998	Kato et al.	257	72	
	5	8	0	8	3	1	8	09/1998	Masumo et al.	257	72	
	5	8	0	8	5	9	5	9/15/98	Kubota et al.	345	92	
	5	9	0	3	0	1	4	5/11/99	Ino et al.	257	66	
	5	9	4	2	8	5	6	08/1999	Koyama	315	169.3	
	5	9	4	3	5	9	3	08/1999	Noguchi et al.	438	487	
	5	9	6	0	3	2	3	9/99	Wakita et al.			
	5	9	8	1	9	7	4	11/9/99	Makita	257	72	
	6	0	2	8	5	7	7	2/22/00	Sakamoto	345	92	
SWL	6	0	3	7	9	2	4	3/14/00	Koyama et al.	345	92	

FOREIGN PATENT DOCUMENTS													
	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation	
												YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
SWL	Kubo et al., "Characteristics of Polycrystalline-Si Thin Film Transistors Fabricated by Excimer Laser Annealing Method", IEEE Transactions on Electron Devices, Oct. 1994, pp. 1876-1879
SWL	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD With Low Temperature Processing", IEEE Transactions on Electron Devices, Feb. 1995, pp. 251-257
SWL	Kuriyama, "Excimer Laser Crystallization of Silicon Films for AMLCDs", AMLCK Second International Workshop on Active Matrix Liquid Crystal Displays, Sept. 1995, pp. 87-92

EXAMINER CRANE	DATE CONSIDERED 5/31/02
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